Jan Van Houdt

List of Publications by Year
in descending order

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30 papers	413 citations	759233 12 h-index	794594 19 g-index
31 all docs	31 docs citations	31 times ranked	422 citing authors

#	Article	IF	Citations
1	Impacts of Pulsing Schemes on the Endurance of Ferroelectric Metalâ€“Ferroelectricâ€“Insulatorâ€“Semiconductor Capacitors. IEEE Journal of the Electron Devices Society, 2022, 10, 109-114.	2.1	2
2	High-Endurance Ferroelectric (La, Y) and (La, Gd) Co-Doped Hafnium Zirconate Grown by Atomic Layer Deposition. ACS Applied Electronic Materials, 2022, 4, 1823-1831.	4.3	15
3	Trap-polarization interaction during low-field trap characterization on hafnia-based ferroelectric gatestacks. , 2022, , .		3
4	A comprehensive variability study of doped HfO₂ FeFET for memory applications. , 2022, , .		3
5	Electrical Investigation of Wake-Up in High Endurance Fatigue-Free La and Y Doped HZO Metalâ€“Ferroelectricâ€“Metal Capacitors. IEEE Transactions on Electron Devices, 2022, 69, 4744-4749.	3.0	14
6	First principles investigation of charge transition levels in monoclinic, orthorhombic, tetragonal, and cubic crystallographic phases of HfO2. Journal of Applied Physics, 2021, 129, .	2.5	17
7	Ferroelectric Laâ€Doped ZrO₂/Hf_xZr_{1â^’x}O₂ Bilayer Stacks with Enhanced Endurance. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100033.	2.4	11
8	Compact Modeling of Multidomain Ferroelectric FETs: Charge Trapping, Channel Percolation, and Nucleation-Growth Domain Dynamics. IEEE Transactions on Electron Devices, 2021, 68, 2107-2115.	3.0	21
9	Understanding the memory window in 1T-FeFET memories: a depolarization field perspective. , 2021, , .		5
10	Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous Pâ€“V and Iâ€“V in HfOâ„‚-Based Ferroelectric FET. IEEE Transactions on Electron Devices, 2021, 68, 4391-4396.	3.0	10
11	Program/Erase Scheme for Suppressing Interface Trap Generation in HfO₂-Based Ferroelectric Field Effect Transistor. IEEE Electron Device Letters, 2021, 42, 1280-1283.	3.9	12
12	Low-frequency noise assessment of ferro-electric field-effect transistors with Si-doped HfO2 gate dielectric. AIP Advances, 2021, 11, .	1.3	4
13	Strain and ferroelectricity in wurtzite ScxAl1â^’xN materials. Applied Physics Letters, 2021, 119, .	3.3	11
14	Defect profiling in FEFET Si:HfO2 layers. Applied Physics Letters, 2020, 117, .	3.3	23
15	Probing the Evolution of Electrically Active Defects in Doped Ferroelectric HfO2 during Wake-Up and Fatigue. , 2020, , .		6
16	Investigation of Imprint in FE-HfOâ„‚ and Its Recovery. IEEE Transactions on Electron Devices, 2020, 67, 4911-4917.	3.0	18
17	Endurance of ferroelectric La-doped HfO2 for SFS gate-stack memory devices. , 2020, , .		1
18	Impact of Ferroelectric Wakeup on Reliability of Laminate based Si-doped Hafnium Oxide (HSO) FeFET Memory Cells. , 2020, , .		7

#	Article	IF	Citations
19	Identifying alternative ferroelectric materials beyond Hf(Zr)O2. Applied Physics Letters, 2020, 117, 262903.	3.3	3
20	Impact of interface layer on charge trapping in Si:HfO₂ based FeFET. , 2020, , .		0
21	Positive non-linear capacitance: the origin of the steep subthreshold-slope in ferroelectric FETs. Scientific Reports, 2019, 9, 14957.	3.3	14
22	New Insights into the Imprint Effect in FE-HfO₂ and its Recovery. , 2019, , .		12
23	On the Characterization and Separation of Trapping and Ferroelectric Behavior in HfZrO FET. IEEE Journal of the Electron Devices Society, 2019, 7, 855-862.	2.1	39
24	Physical Insights on Steep Slope FEFETs including Nucleation-Propagation and Charge Trapping. , 2019, , .		12
25	Physical Model for the Steep Subthreshold Slope in Ferroelectric FETs. IEEE Electron Device Letters, 2018, 39, 877-880.	3.9	27
26	Reliability Study of Ferroelectric Al:HfO₂Thin Films for DRAM and NAND Applications. IEEE Transactions on Electron Devices, 2017, 64, 4091-4098.	3.0	56
27	Trades-off between lithography line edge roughness and error-correcting codes requirements for NAND Flash memories. Microelectronics Reliability, 2012, 52, 525-529.	1.7	2
28	Charge-based nonvolatile memory: Near the end of the roadmap?. Current Applied Physics, 2011, 11, e21-e24.	2.4	18
29	Cross-cell interference variability aware model of fully planar NAND Flash memory including line edge roughness. Microelectronics Reliability, 2011, 51, 919-924.	1.7	31
30	Physical understanding and modeling of SANOS retention in programmed state. Solid-State Electronics, 2008, 52, 577-583.	1.4	16